E S Bielejec

List of Publications by Year
in descending order

41 papers	1,920 citations	567281 15 h-index	276875 41 g-index
41 all docs	41 docs citations	41 times ranked	2270 citing authors

#	Article	IF	Citations
1	Imaging dark charge emitters in diamond via carrier-to-photon conversion. Science Advances, 2022, 8, eabl9402.	10.3	9
2	Nanoscale solid-state nuclear quadrupole resonance spectroscopy using depth-optimized nitrogen-vacancy ensembles in diamond. Applied Physics Letters, 2022, 120, .	3.3	11
3	Coherent Interactions between Silicon-Vacancy Centers in Diamond. Physical Review Letters, 2022, 128, .	7.8	2
4	Lithium source for focused ion beam implantation and analysis. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2021, 39, .	1.2	4
5	Impact of Surface Recombination on Single-Event Charge Collection in an SOI Technology. IEEE Transactions on Nuclear Science, 2021, 68, 305-311.	2.0	7
6	Hidden Silicon-Vacancy Centers in Diamond. Physical Review Letters, 2021, 126, 213601.	7.8	10
7	Investigating Heavy-Ion Effects on 14-nm Process FinFETs: Displacement Damage Versus Total Ionizing Dose. IEEE Transactions on Nuclear Science, 2021, 68, 724-732.	2.0	8
8	Heavy-Ion-Induced Displacement Damage Effects in Magnetic Tunnel Junctions With Perpendicular Anisotropy. IEEE Transactions on Nuclear Science, 2021, 68, 581-587.	2.0	9
9	Irradiation Effects on Perpendicular Anisotropy Spinâ€“Orbit Torque Magnetic Tunnel Junctions. IEEE Transactions on Nuclear Science, 2021, 68, 665-670.	2.0	13
10	Using silicon-vacancy centers in diamond to probe the full strain tensor. Journal of Applied Physics, 2021, 130, 024301.	2.5	2
11	Optical activation and detection of charge transport between individual colour centres in diamond. Nature Electronics, 2021, 4, 717-724.	26.0	23
12	Photocurrent From Single Collision 14-MeV Neutrons in GaN and GaAs. IEEE Transactions on Nuclear Science, 2020, 67, 221-227.	2.0	1
13	Large-scale integration of artificial atoms in hybrid photonic circuits. Nature, 2020, 583, 226-231.	27.8	248
14	Controlling light emission by engineering atomic geometries in silicon photonics. Optics Letters, 2020, 45, 1631.	3.3	9
15	Comparison of Radiation Effects in Custom and Commercially Fabricated Resistive Memory Devices. IEEE Transactions on Nuclear Science, 2019, 66, 2398-2407.	2.0	2
16	Failure Thresholds in CBRAM Due to Total Ionizing Dose and Displacement Damage Effects. IEEE Transactions on Nuclear Science, 2019, 66, 69-76.	2.0	2
17	Training a Neural Network on Analog TaO_{<italic>x</italic>} ReRAM Devices Irradiated With Heavy Ions: Effects on Classification Accuracy Demonstrated With CrossSim. IEEE Transactions on Nuclear Science, 2019, 66, 54-60.	2.0	8
18	Stochastic Gain Degradation in IIIâ€“V Heterojunction Bipolar Transistors Due to Single Particle Displacement Damage. IEEE Transactions on Nuclear Science, 2018, 65, 206-210.	2.0	3

#	ARTICLE	IF	CITATIONS
19	Photon-mediated interactions between quantum emitters in a diamond nanocavity. Science, 2018, 362, 662-665.	12.6	189
20	Strain engineering of the silicon-vacancy center in diamond. Physical Review B, 2018, 97, .	3.2	171
21	Bright nanowire single photon source based on SiV centers in diamond. Optics Express, 2018, 26, 80.	3.4	37
22	Scalable focused ion beam creation of nearly lifetime-limited single quantum emitters in diamond nanostructures. Nature Communications, 2017, 8, 15376.	12.8	141
23	Fiber-Coupled Diamond Quantum Nanophotonic Interface. Physical Review Applied, 2017, 8, .	3.8	115
24	Ion implantation for deterministic single atom devices. Review of Scientific Instruments, 2017, 88, 123301.	1.3	41
25	An integrated diamond nanophotonics platform for quantum-optical networks. Science, 2016, 354, 847-850.	12.6	570
26	Sub-Micron Resolution of Localized Ion Beam Induced Charge Reduction in Silicon Detectors Damaged by Heavy Ions. IEEE Transactions on Nuclear Science, 2015, 62, 2919-2925.	2.0	2
27	Mapping of Radiation-Induced Resistance Changes and Multiple Conduction Channels in <formula formulatype="inline"> <tex Notation="TeX">${m TaO}_{m x}$</tex></formula> Memristors. IEEE Transactions on Nuclear Science, 2014, 61, 2965-2971.	2.0	5
28	Experimental Study of Defect Formations in GaAs Devices Using Gain, Photoluminescence and Deep Level Transient Spectroscopy. IEEE Transactions on Nuclear Science, 2013, 60, 219-223.	2.0	1
29	A Comparison of the Radiation Response of ${m TaO}_{m x}$ and ${m TiO}_2$ Memristors. IEEE Transactions on Nuclear Science, 2013, 60, 4512-4519.	2.0	37
30	Initial Assessment of the Effects of Radiation on the Electrical Characteristics of ${m TaO}_{m x}$ Memristive Memories. IEEE Transactions on Nuclear Science, 2012, 59, 2987-2994.	2.0	69
31	Continuous distribution of defect states and band gap narrowing in neutron irradiated GaAs. Journal of Applied Physics, 2010, 107, .	2.5	9
32	Tunneling spectroscopy in vertically coupled quantum wires. Solid State Communications, 2008, 147, 79-82.	1.9	3
33	Comparison Between Experimental and Simulation Results for Ion Beam and Neutron Irradiations in Silicon Bipolar Junction Transistors. IEEE Transactions on Nuclear Science, 2008, 55, 3055-3059.	2.0	6
34	Defect-driven gain bistability in neutron damaged, silicon bipolar transistors. Applied Physics Letters, 2007, 90, 172105.	3.3	38
35	Metrics for Comparison Between Displacement Damage due to Ion Beam and Neutron Irradiation in Silicon BJTs. IEEE Transactions on Nuclear Science, 2007, 54, 2282-2287.	2.0	14
36	Nonlinear resonant tunneling in low-dimensional systems in a magnetic field: Energy dispersion. Physica E: Low-Dimensional Systems and Nanostructures, 2006, 34, 425-428.	2.7	4

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37	Tunneling and nonlinear transport in a low-dimensional vertically coupled GaAs/AlGaAs system. Physica E: Low-Dimensional Systems and Nanostructures, 2006, 34, 433-436.	2.7	5
38	Damage Equivalence of Heavy Ions in Silicon Bipolar Junction Transistors. IEEE Transactions on Nuclear Science, 2006, 53, 3681-3686.	2.0	23
39	0.7 structure in long quantum wires. Superlattices and Microstructures, 2003, 34, 493-496.	3.1	1
40	Field-Tuned Superconductor-Insulator Transition with and without Current Bias. Physical Review Letters, 2002, 88, 206802.	7.8	46
41	Electron Glass in Ultrathin Granular Al Films at Low Temperatures. Physical Review Letters, 2001, 87, 256601.	7.8	22